

## N-Channel 100-V (D-S) MOSFET

## **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

<b>Typical</b>	App	licatior	าร:
----------------	-----	----------	-----

- LED Inverter Circuits
- DC/DC Conversion Circuits
- Motor drives

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)	
100	2000 @ V <sub>GS</sub> = 10V	0.66	
	2200 @ V <sub>GS</sub> = 5.5V	0.63	







ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)					
Parameter			Limit	Units	
Drain-Source Voltage		$V_{DS}$	100	V	
Gate-Source Voltage			±20	V	
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> =25°C	I <sub>D</sub>	0.66		
Continuous Drain Current	T <sub>A</sub> =70°C	טי	0.52	Α	
Pulsed Drain Current <sup>b</sup>			3		
Continuous Source Current (Diode Conduction) a	I <sub>S</sub>	0.66	Α		
Power Dissipation <sup>a</sup>	T <sub>A</sub> =25°C	$P_{D}$	1.3	W	
Power Dissipation	T <sub>A</sub> =70°C	' D	0.8	VV	
Operating Junction and Storage Temperature Range		$T_J,T_stg$	-55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter			Maximum	Units	
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	$R_{\theta JA}$	100	°C/W	
Maximum Junction-to-Ambient	Steady State	IΛθΊΑ	166	C/VV	

#### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

# MI2372N

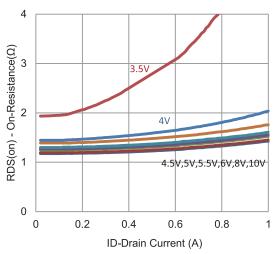
## **Electrical Characteristics**

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250 \text{ uA}$	1			V
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±10	uA
Zero Gate Voltage Drain Current		$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA
Leto Gate Voltage Brain Current	DSS	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	1			Α
Drain Course On Besistance a	r	$V_{GS} = 10 \text{ V}, I_D = 0.5 \text{ A}$			2000	0
Drain-Source On-Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS} = 5.5 \text{ V}, I_D = 0.4 \text{ A}$			2200	mΩ
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15 \text{ V}, I_{D} = 0.5 \text{ A}$		4		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_{S} = 0.33 \text{ A}, V_{GS} = 0 \text{ V}$		0.79		V
		Dynamic <sup>b</sup>				
Total Gate Charge	$Q_g$	$V_{DS} = 50 \text{ V}, V_{GS} = 4.5 \text{ V},$		1.2		
Gate-Source Charge	$Q_{gs}$	$I_{DS} = 30 \text{ V}, \text{ V}_{GS} = 4.3 \text{ V},$ $I_{D} = 0.5 \text{ A}$		0.2		nC
Gate-Drain Charge	$Q_{gd}$	I <sub>D</sub> – 0.5 A		0.8		
Turn-On Delay Time	t <sub>d(on)</sub>	$V_{DS} = 50 \text{ V}, R_{L} = 100 \Omega,$		2		
Rise Time	t <sub>r</sub>	$V_{DS} = 50 \text{ V}, R_L = 100 \Omega,$ $I_D = 0.5 \text{ A},$ $V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		4		ne
Turn-Off Delay Time	$t_{d(off)}$			12		ns
Fall Time	t <sub>f</sub>			5		
Input Capacitance	C <sub>iss</sub>			61		
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		19		рF
Reverse Transfer Capacitance	$C_{rss}$			9		

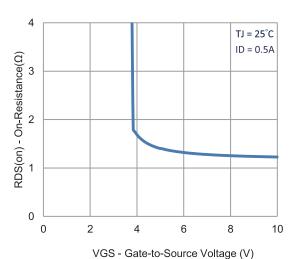
#### Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

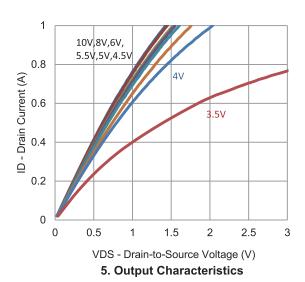
## **Typical Electrical Characteristics**

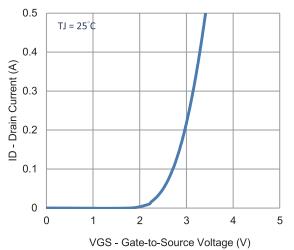


#### 1. On-Resistance vs. Drain Current

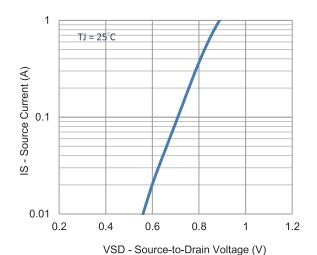


3. On-Resistance vs. Gate-to-Source Voltage

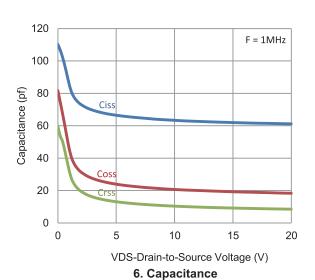




2. Transfer Characteristics



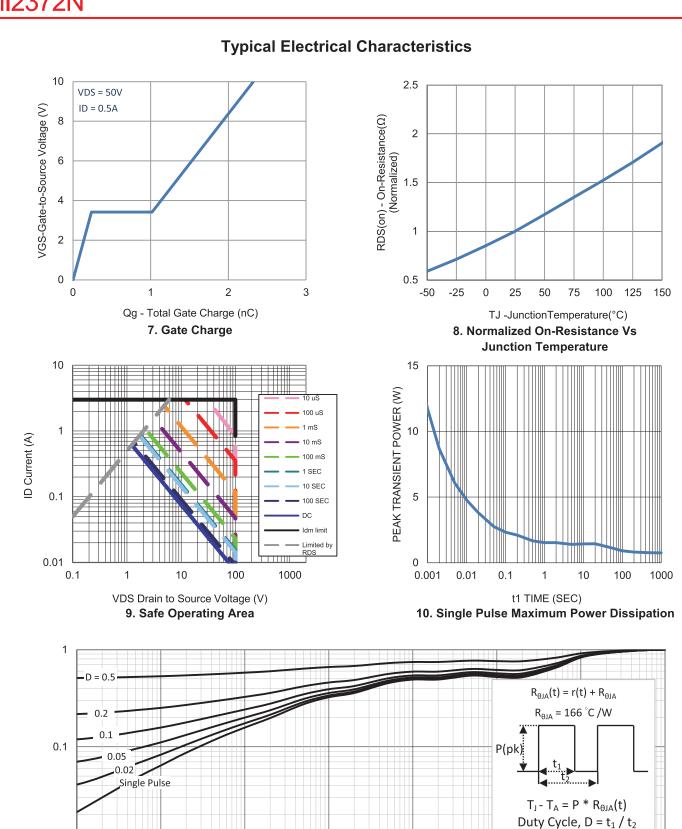
4. Drain-to-Source Forward Voltage



0.0001

0.001

0.01



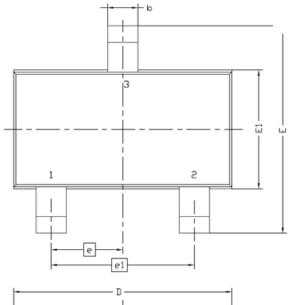
1000

100

10

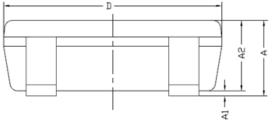
0.1

## **Package Information**



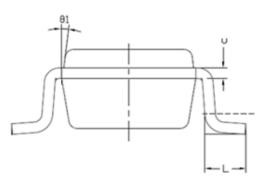
I Symbol I			
Symbol	MIN	MAX	
Α	8.0	1.2	
A1	0	0.1	
A2	0.7	1.1	
b	0.3	0.5	
С	0.1	0.2	
D	2.7	3.1	
E	2.6	3	
E1	1.4	1.8	
е	0.95 BSC		
e1	1.9 BSC		
Ĺ	0.3	0.6	
θ1	7° NOM		
	<u> </u>		

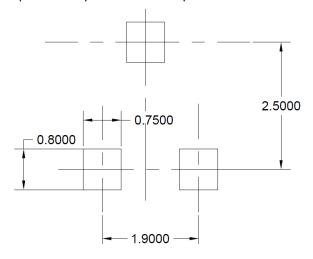
Gundad MILLIMETERS



## **Recommended Pad Layout**

Note: Drain opening is recommended to be solder mask defined in a copper fill to provide improved thermal performance





Analog Power (APL) reserves the right to make changes without further notice to any products herein. APL makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does APL assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in APL data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. APL does not convey any license under its patent rights nor the rights of others. APL products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the APL product could create a situation where personal injury or death may occur. Should Buyer purchase or use APL products for any such unintended or unauthorized application, Buyer shall indemnify and hold APL and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that APL was negligent regarding the design or manufacture of the part. APL is an Equal Opportunity/Affirmative Action Employer.